



# FDN340P

## Single P-Channel, Logic Level, PowerTrench® MOSFET

### General Description

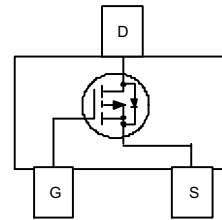
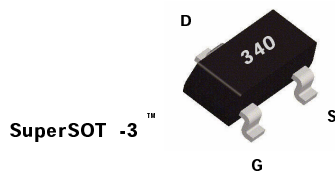
This P-Channel Logic Level MOSFET is produced using Fairchild Semiconductor advanced Power Trench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

These devices are well suited for portable electronics applications: load switching and power management, battery charging circuits, and DC/DC conversion.



### Features

- -2A, 20 V  $R_{DS(ON)} = 70 \text{ m}\Omega @ V_{GS} = -4.5 \text{ V}$   
 $R_{DS(ON)} = 110 \text{ m}\Omega @ V_{GS} = -2.5 \text{ V}$
- Low gate charge (7.2 nC typical).
- High performance trench technology for extremely low  $R_{DS(ON)}$ .
- High power version of industry Standard SOT-23 package. Identical pin-out to SOT-23 with 30% higher power handling capability.



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	-20	V
$V_{GSS}$	Gate-Source Voltage	$\pm 8$	V
$I_b$	Drain Current – Continuous (Note 1a)	-2	A
	– Pulsed	-10	
$P_D$	Power Dissipation for Single Operation (Note 1a) (Note 1b)	0.5	W
		0.46	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	250	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	75	$^\circ\text{C/W}$

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
340	FDN340P	7"	8mm	3000 units

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_b = -250\ \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_b = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-12		mV/°C
$I_{bSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$			-10	
$I_{GSSF}$	Gate–Body Leakage, Forward	$V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate–Body Leakage, Reverse	$V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
<b>On Characteristics (Note 2)</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_b = -250\ \mu\text{A}$	-0.4	-0.8	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_b = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		3		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5\text{ V}, I_b = -2\text{ A}$		60	70	m $\Omega$
		$V_{GS} = -4.5\text{ V}, I_b = -2\text{ A}, T_J = 125^\circ\text{C}$		77	120	
		$V_{GS} = -2.5\text{ V}, I_b = -1.7\text{ A}$		82	110	
$I_{b(on)}$	On–State Drain Current	$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-5			A
$g_{FS}$	Forward Transconductance	$V_{DS} = -4.5\text{ V}, I_b = -2\text{ A}$		9		S
<b>Dynamic Characteristics</b>						
$C_{ISS}$	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		779		pF
$C_{OSS}$	Output Capacitance			121		pF
$C_{RSS}$	Reverse Transfer Capacitance			56		pF
<b>Switching Characteristics (Note 2)</b>						
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -10\text{ V}, I_b = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$		10	20	ns
$t_r$	Turn–On Rise Time			9	10	
$t_{d(off)}$	Turn–Off Delay Time			27	43	
$t_f$	Turn–Off Fall Time			11	20	
$Q_g$	Total Gate Charge	$V_{DS} = -10\text{ V}, I_b = -3.5\text{ A},$ $V_{GS} = -4.5\text{ V}$		7.2	10	nC
$Q_{gs}$	Gate–Source Charge			1.7		
$Q_{gd}$	Gate–Drain Charge			1.5		
<b>Drain–Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain–Source Diode Forward Current				-0.42	A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -0.42\text{ A}$ (Note 2)		-0.7	-1.2	V

**Notes:**

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a.  $250^\circ\text{C/W}$  when mounted on a  $0.02\text{ in}^2$  pad of 2 oz copper



b.  $270^\circ\text{C/W}$  when mounted on a  $.001\text{ in}^2$  pad of 2 oz copper

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width <  $300\ \mu\text{s}$ , Duty Cycle < 2.0%

## Typical Characteristics

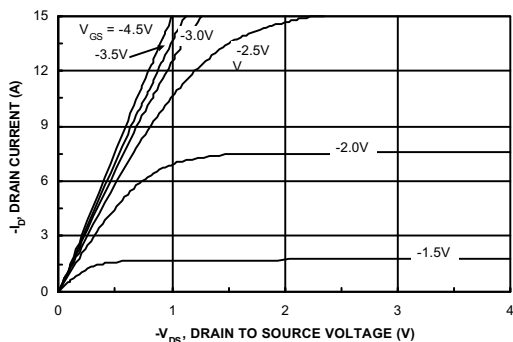


Figure 1. On-Region Characteristics.

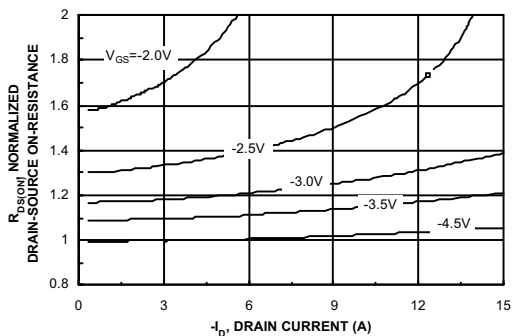


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

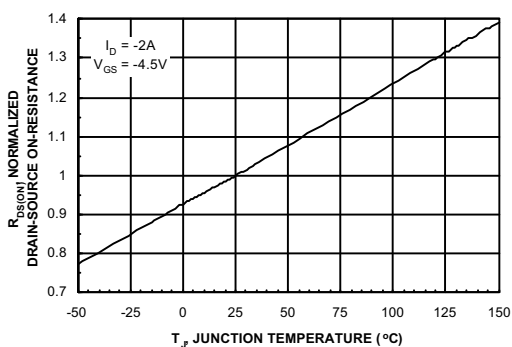


Figure 3. On-Resistance Variation with Temperature.

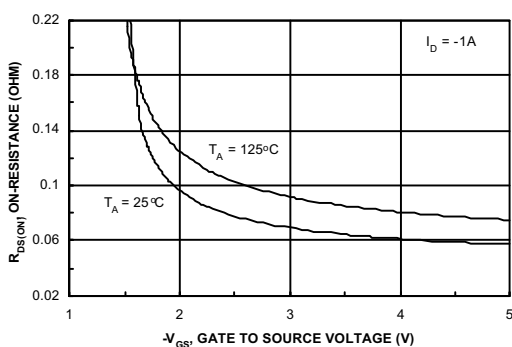


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

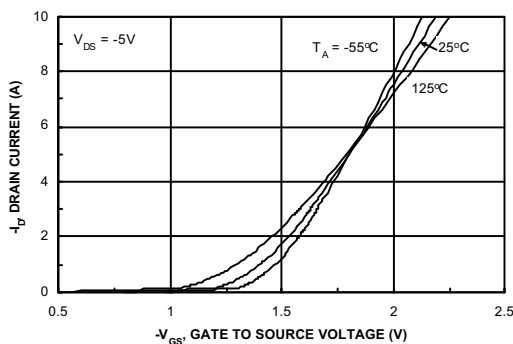


Figure 5. Transfer Characteristics.

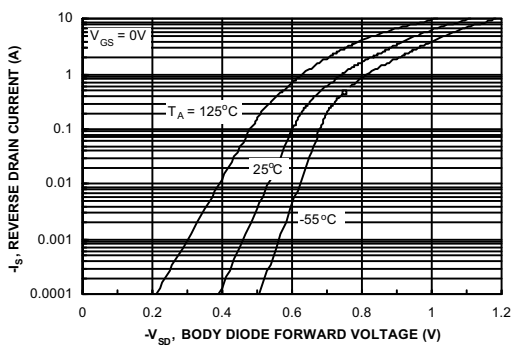
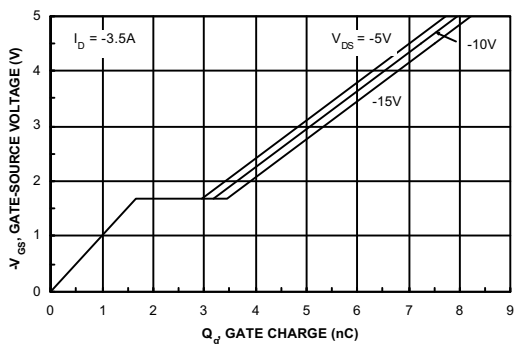
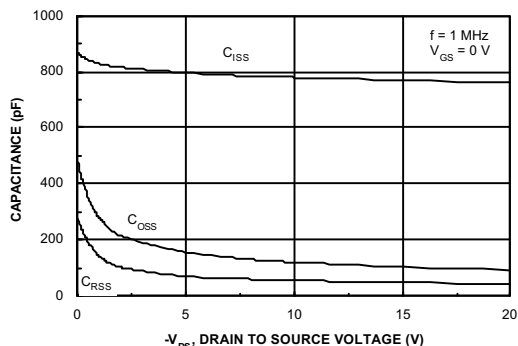


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

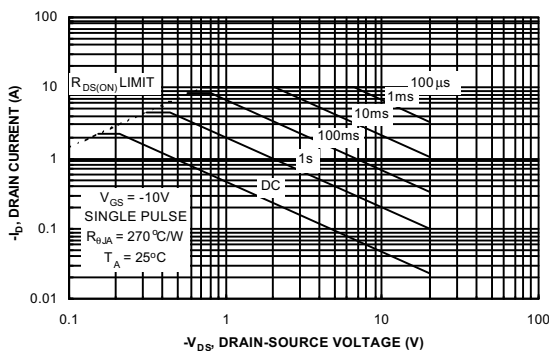
## Typical Characteristics



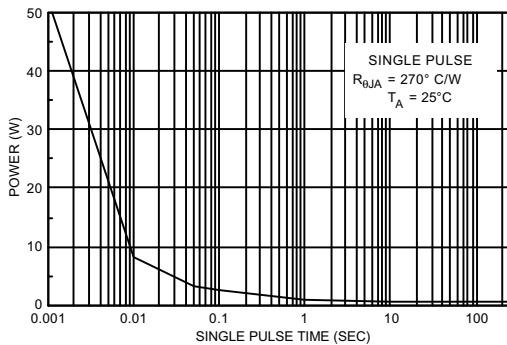
**Figure 7. Gate Charge Characteristics.**



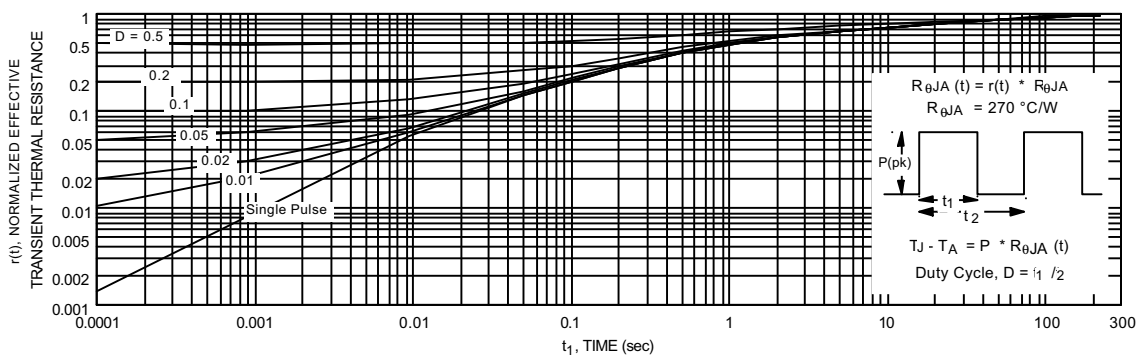
**Figure 8. Capacitance Characteristics.**



**Figure 9. Maximum Safe Operating Area.**



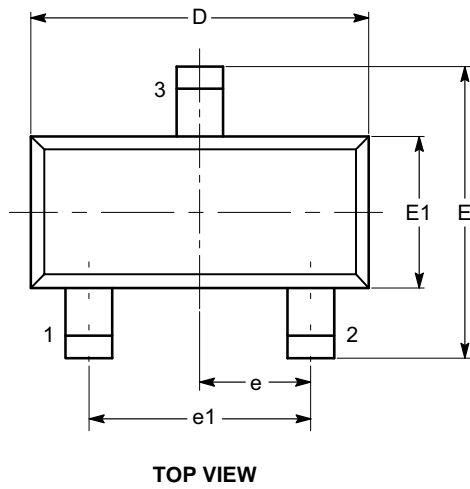
**Figure 10. Single Pulse Maximum Power Dissipation.**



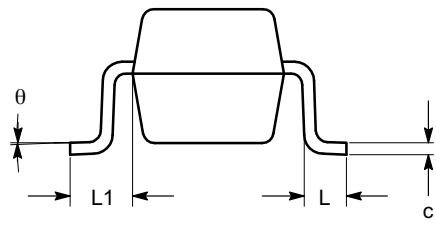
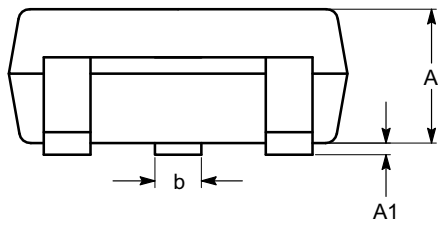
**Figure 11. Transient Thermal Response Curve.**

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

**SOT-23, 3 Lead**  
CASE 527AG-01  
ISSUE O



SYMBOL	MIN	NOM	MAX
A	0.89		1.12
A1	0.013		0.10
b	0.37		0.50
c	0.085		0.18
D	2.80		3.04
E	2.10		2.64
E1	1.20		1.40
e	0.95 BSC		
e1	1.90 BSC		
L	0.40 REF		
L1	0.54 REF		
$\theta$	0°		8°



**Notes:**

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC TO-236.

## Dimensional Outline and Pad Layout

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